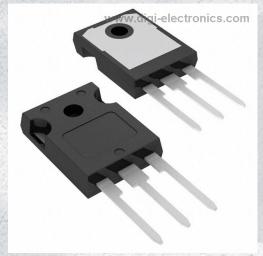


# MJW18020G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MJW18020G-DG

Manufacturer onsemi

Manufacturer Product Number MJW18020G

Description TRANS NPN 450V 30A TO247-3

Detailed Description Bipolar (BJT) Transistor NPN 450 V 30 A 13MHz 250

W Through Hole TO-247-3



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RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MJW18020G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	30 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
450 V	1.5V @ 4A, 20A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100μΑ	14 @ 3A, 5V
Power - Max:	Frequency - Transition:
250 W	13MHz
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-247-3	TO-247-3
Base Product Number:	
MJW18020	

# **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



## NPN Silicon Power Transistors High Voltage Planar

## MJW18020

The MJW18020 planar High Voltage Power Transistor is specifically Designed for motor control applications, high power supplies and UPS's for which the high reproducibility of DC and Switching parameters minimizes the dead time in bridge configurations.

#### **Features**

- High and Excellent Gain Linearity
- Fast and Very Tight Switching Times Parameters tsi and tfi
- Very Stable Leakage Current due to the Planar Structure
- High Reliability
- Pb-Free Package is Available\*

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V <sub>CEO</sub>	450	Vdc
Collector-Emitter Breakdown Voltage	V <sub>CES</sub>	1000	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	1000	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	9.0	Vdc
Collector Current - Continuous - Peak (Note 1)	IC	30 45	Adc
Base Current - Continuous - Peak (Note 1)	I <sub>B</sub>	6.0 10	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	250 2.0	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C

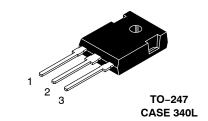
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5  $\mu$ s, Duty Cycle  $\leq$  10%.

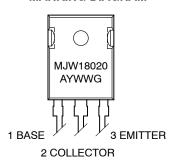
# \*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

1

## 30 AMPERES 1000 VOLTS BV<sub>CES</sub> 450 VOLTS BV<sub>CEO,</sub> 250 WATTS



#### **MARKING DIAGRAM**



Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

## **ORDERING INFORMATION**

Device	Package	Shipping
MJW18020	TO-247	30 Units/Rail
MJW18020G	TO-247 (Pb-Free)	30 Units/Rail

## MJW18020

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characte	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	450	_	-	Vdc	
Collector Cutoff Current (V <sub>CE</sub> = Rated V <sub>CEO</sub> , I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	_	100	μAdc	
Collector Cutoff Current (V <sub>CE</sub> = Rated V <sub>C</sub> (T <sub>C</sub> = 125°C)	<sub>ES</sub> , V <sub>EB</sub> = 0)	I <sub>CES</sub>	-	-	100 500	μAdc
Emitter Cutoff Current (V <sub>CE</sub> = 9 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	_	100	μAdc
ON CHARACTERISTICS					•	
DC Current Gain (I <sub>C</sub> = 3 Adc, V <sub>CE</sub> = 5	Vdc) (T <sub>C</sub> = 125°C)	h <sub>FE</sub>	14	30	34 -	
$(I_C = 10 \text{ Adc } V_{CE} = 2)$	Vdc)		8	16 14		
$(I_C = 20 \text{ Adc } V_{CE} = 2)$			5 5.5	9	_	
$(I_C = 10 \text{ mAdc V}_{CE} =$	$(T_C = 125^{\circ}C)$ 5 Vdc)		4 14	7 25	-	
Base–Emitter Saturation Voltage ( $I_C = 10$ ) ( $I_C = 20$ )	) Adc, I <sub>B</sub> = 2 Adc) ) Adc, I <sub>B</sub> = 4 Adc)	V <sub>BE(sat)</sub>	-	0.97 1.15	1.25 1.5	Vdc
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>				Vdc	
$(I_C = 10 \text{ Adc}, I_B = 2 \text{ Adc})$		_	0.2 0.3	0.6		
$(I_C = 20 \text{ Adc}, I_B = 4 \text{ Adc})$		-	0.5	1.5		
DVALANIO QUADA OTERIOTICO	(T <sub>C</sub> = 125°C)		_	0.9	2.0	
DYNAMIC CHARACTERISTICS  Current Gain Bandwidth Product		f.	1	13	1	MHz
$(I_C = 1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 1 \text{ MI})$	f <sub>T</sub>	_	13	_	IVITIZ	
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f_{test} = 1 \text{ MHz})$	C <sub>ob</sub>	-	300	500	pF	
Input Capacitance (V <sub>EB</sub> = 8.0)	C <sub>ib</sub>	_	7000	9000	pF	
SWITCHING CHARACTERISTICS: Resi	stive Load (D.C. = 10%, Pulse Width	= 70 μs)	II.	l	I.	
Turn-On Time	$(I_C = 10 \text{ Adc}, I_{B1} = I_{B2} = 2 \text{ Adc},$	t <sub>On</sub>	_	540	750	ns
Storage Time	Vcc = 125 V)	t <sub>s</sub>	_	4.75	6	μs
Fall Time		t <sub>f</sub>	_	380	500	ns
Turn-Off Time		t <sub>Off</sub>	_	5.2	6.5	μs
Turn-On Time	$(I_C = 20 \text{ Adc}, I_{B1} = I_{B2} = 4 \text{ Adc},$	t <sub>On</sub>	_	965	1200	ns
Storage Time	Vcc = 125 V)	t <sub>s</sub>	_	2.9	3.5	μs
Fall Time		t <sub>f</sub>	_	350	500	ns
Turn-Off Time			-	3.25	4	μs
SWITCHING CHARACTERISTICS: Indu	ctive Load (V <sub>clamp</sub> = 300 V , Vcc = 15	5 V, L = 200 μH)				
Fall Time	$(I_C = 10 \text{ Adc}, I_{B1} = I_{B2} = 2 \text{ Adc})$	t <sub>fi</sub>	-	142	250	ns
Storage Time		t <sub>si</sub>	-	4.75	6	μs
_	t <sub>C</sub>	-	320	500	ns	
Crossover Time				1	<b>.</b>	
Crossover Time Fall Time	(I <sub>C</sub> = 20 Adc, I <sub>B1</sub> = I <sub>B2</sub> = 4 Adc)	t <sub>fi</sub>	-	350	500	ns
	(I <sub>C</sub> = 20 Adc, I <sub>B1</sub> = I <sub>B2</sub> = 4 Adc)	t <sub>fi</sub>	-	350 3.0	500 3.5	ns µs

## MJW18020

## **TYPICAL CHARACTERISTICS**

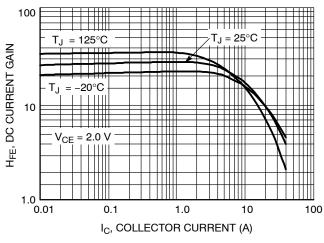


Figure 1. DC Current Gain, V<sub>CE</sub> = 2.0 V

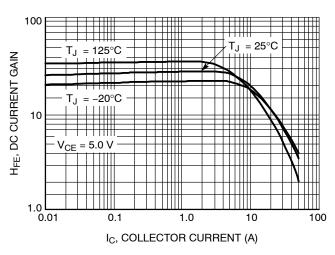


Figure 2. DC Current Gain, V<sub>CE</sub> = 5.0 V

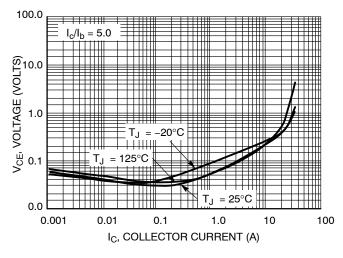


Figure 3. Typical Collector–Emitter Saturation Voltage,  $I_C/I_B = 5.0$ 

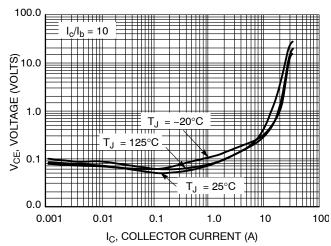


Figure 4. Typical Collector–Emitter Saturation Voltage,  $I_C/I_B = 10$ 

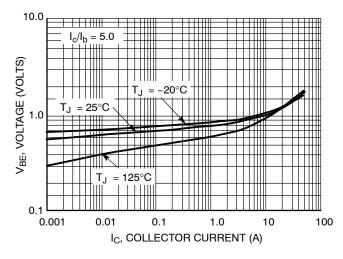


Figure 5. Typical Base–Emitter Saturation Voltage,  $I_C/I_B = 5.0$ 

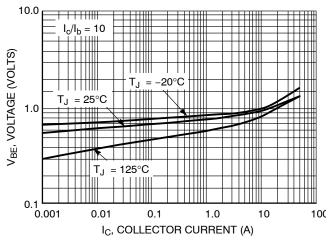


Figure 6. Typical Base–Emitter Saturation Voltage, I<sub>C</sub>/I<sub>B</sub> = 10

## MJW18020

## **TYPICAL CHARACTERISTICS**

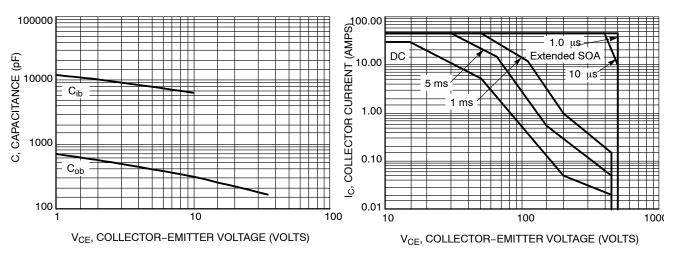


Figure 7. Typical Capacitance

Figure 8. Forward Bias Safe Operating Area

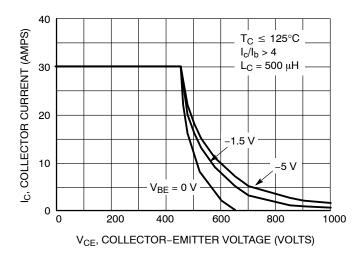
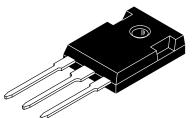


Figure 9. Reverse Bias Safe Operating Area



## MECHANICAL CASE OUTLINE

**PACKAGE DIMENSIONS** 



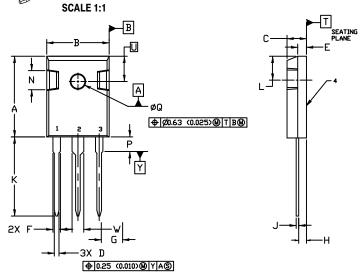
TO-247 CASE 340L ISSUE G

**DATE 06 OCT 2021** 

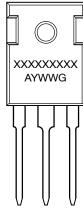
#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER

	MILLIMETERS		INC	HES	
DIM	MIN.	MAX.	MIN.	MAX.	
Α	20.32	21.08	0.800	0.830	
В	15.75	16.26	0.620	0.640	
С	4.70	5.30	0.185	0.209	
D	1.00	1.40	0.040	0.055	
Ε	1.90	2.60	0.075	0.102	
F	1.65	2.13	0.065	0.084	
G	5.45	5.45 BSC		0.215 BSC	
Н	1.50	2.49	0.059	0.098	
J	0.40	0.80	0.016	0.031	
К	19.81	20.83	0.780	0.820	
L	5.40	6.20	0.212	0.244	
N	4.32	5.49	0.170	0.216	
Р		4.50		0.177	
Q	3.55	3.65	0.140	0.144	
U	6.15 BSC		0.242	BSC	
W	2.87	3.12	0.113	0.123	



# GENERIC MARKING DIAGRAM\*



STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

> PIN 1. CATHODE 2. ANODE

3. GATE 4. ANODE

STYLE 5:

STYLE 2:
PIN 1. ANODE
2. CATHODE (S)
3. ANODE 2
4. CATHODES (S)

PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2

3. GATE 4. MAIN TERMINAL 2

STYLE 6:

STYLE 3:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

XXXXX = Specific Device Code A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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